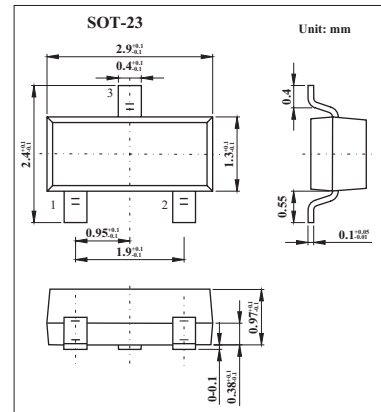


BAV199

■ Features

- Plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μs
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.



■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Conditions	Min	Max	Unit
Repetitive peak reverse voltage	V _{RRM}			85	V
Continuous reverse voltage	V _R			75	V
Continuous forward current	I _F	single diode loaded		160	mA
		double diode loaded		140	
Repetitive peak forward current	I _{FRM}			500	mA
Non-repetitive peak forward current	I _{FSM}	square wave; T _j = 25 °C prior to surge;			A
		t = 1 μs		4	
		t = 1 ms		1	
		t = 1 s		0.5	
Total power dissipation	P _{tot}	T _{amb} = 25 °C		250	mW
Storage temperature	T _{stg}		-65	+150	°C
Junction temperature	T _j			150	°C
thermal resistance from junction to tie-point	R _{th j-t p}			360	K/W
thermal resistance from junction to ambient	R _{th j-a}			500	K/W

BAV199

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Typ	Max	Unit
Forward voltage	V_F	$I_F = 1\text{ mA}$		900	mV
		$I_F = 10\text{ mA}$		1000	
		$I_F = 50\text{ mA}$		1100	
		$I_F = 150\text{ mA}$		1250	
Reverse current	I_R	$V_R = 75\text{ V}$	0.003	5	nA
		$V_R = 75\text{ V}; T_j = 150^\circ\text{C}$	3	80	
Diode capacitance	C_d	$f = 1\text{ MHz}; V_R = 0;$	2		pF
Reverse recovery time	t_{rr}	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA};$ $R_L = 100\ \Omega$; measured at $I_R = 1\text{ mA};$	0.8	3	μs

■ Marking

Marking	JYp
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